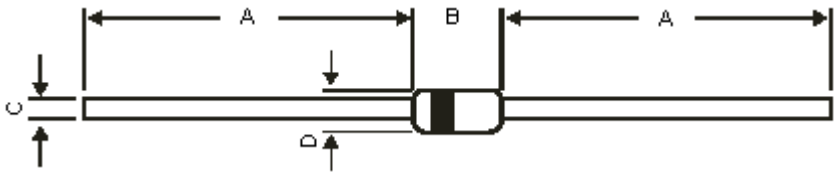
1N4148

Small Signal Diode

Features:

- High speed silicon switching diodes, axial leaded.
- General purpose, industrial, military and space applications.
- Hermetically sealed glass with a stud on either side of the glass passivated chip provides excellent stability.
- Extremely low leakage and very high reliability.

DO-35 Glass Axial Package



NOTE

1. Cathode is marked by Band.

Dimensions	Minimum	Maximum
A	25.40	-
B	3.03	4.44
C	0.46	0.56
D	1.52	2.29

Dimensions : Millimetres

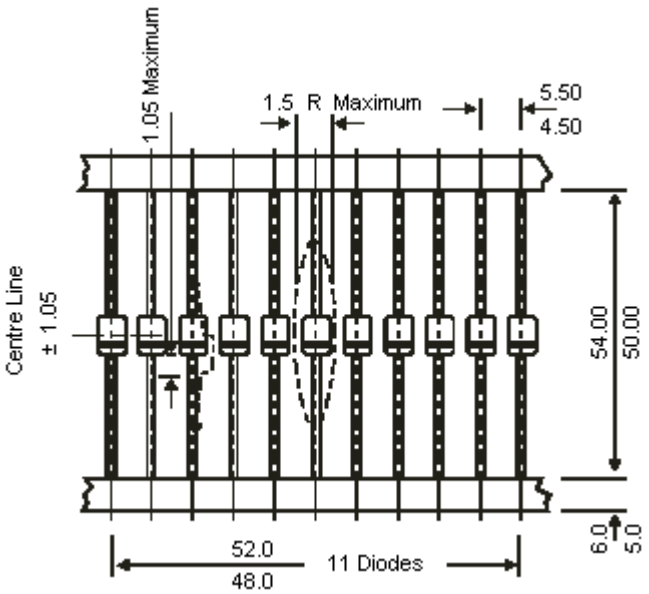
Absolute Maximum Ratings (T_A = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Repetitive Reverse Voltage	U_{RRM}	100	V
Reverse Voltage (Continuous)	U_R	75	
Average Forward Current	$I_{F(AV)}$	150	mA
Forward Current (DC)	I_F	200	
Repetitive Peak Forward Current	I_{FRM}	450	
Non Repetitive Peak Surge Current tp = 1μ second tp = 1 second	I_{FSM}	2000 500	
Power Dissipation Derating Factor	P_{TA}	500 2.85	mW mW/°C
Operating and Storage Junction Temperature Range	T_j, T_{stg}	-65 to +200	°C

Electrical Characteristics (T_a = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Minimum	Maximum	Unit
Forward Voltage	U_F	I_F = 10mA	0.65	1.0	V
Reverse Current	I_R	U_R = 20V U_R = 75V V_R = 20V, T_j = 150°C V_R = 75V, T_j = 150°C	-	25 5.0 50 100	nA µA µA µA
Reverse Breakdown Voltage	U_{BR}	I_R = 100µA	100	-	V
Dynamic Characteristics					
Diode Capacitance	C_d	V_R = 0, f = 1MHz	-	4.0	pF
Forward Recovery Voltage	U_{fr}	I_F = 50mA, t_r = 20ns	-	2.5	V
Reverse Recovery Time	t_{rr}	I_F = 10mA, to I_R = 60mA R_L = 100Ω Measured at I_R = 1mA	-	4.0	ns

DO-35, 52mm Taping Specification



52mm Taping Specification

1. T and A indicates axial tape and ammo packing (52mm tape spacing).
2. 300mm (minimum) leader tape on every spool.
3. Number of empty places allowed 0.25% without consecutive empty places.
4. Ends of leads shall preferably not protrude beyond the tapes.
5. Components shall be held sufficiently in the tape or tapes so that they can not come free in normal handling.